

CD4514B, CD4515B Types

DATA 2

DATA 3 21

DATA 4 22

CD4514B, CD4515B

SCHS074

CMOS 4-Bit Latch/4-to-16

Line Decoders

High-Voltage Types (20-Volt Rating) CD4514B Output "High" on Select CD4515B Output "Low" on Select

CD4514B and CD4515B consist of a 4-bit strobed latch and a 4-to-16-line decoder. The latches hold the last input data presented prior to the strobe transition from 1 to 0. Inhibit control allows all outputs to be placed at 0(CD4514B) or 1(CD4515B) regardless of the state of the data or strobe inputs.

The decode truth table indicates all combinations of data inputs and appropriate selected outputs.

These devices are similar to industry types MC14514 and MC14515.

The CD4514B and CD4515B types are supplied in 24-lead hermetic dual-in-line ceramic packages (D and F suffixes), 24-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).

Features:

- Strobed input latch
- Inhibit control
- 100% tested for quiescent current at 20 V
- Maximum input current of 1 μA at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Noise margin (over full package temperature range):

 $1 \text{ V at V}_{DD} = 5 \text{ V}$

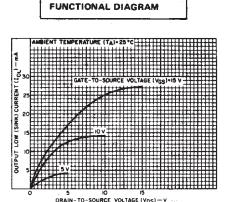
2 V at V_{DD} = 10 V

2.5 V at V_{DD} = 15 V

- 5-V, 10-V, and 15-V parametric ratings
- Standardized, symmetrical output characteristics.
- Meets all requirements of JEDEC Tentative Standard No. 13B; "Standard Specifications for Description of 'B' Series CMOS Devices"

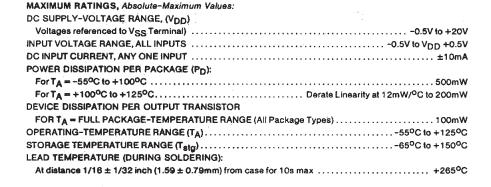
Applications:

- Digital multiplexing
- Address decoding
- Hexadecimal/BCD decoding
- Program-counter decoding
- Control decoder



4 TO 16

Fig. 1 — Typical output low (sink) current characteristics.



RECOMMENDED OPERATING CONDITIONS at $T_A = 25^{\circ}$ C, Except as Noted. For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	V _{DD}	LIN			
CHARACTERISTIC	(V)	Min.	Max.	UNITS	
Supply-Voltage Range (For T _A = Full Package- Temperature Range)		3	18	v	
Data Setup Time, t _S	5 10 15	150 70 40	_ _ _	ns	
Strobe Pulse Width, t _W	5 10 15	250 100 75	_ _ _	ņs	

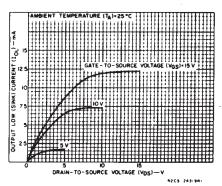


Fig. 2 — Minimum output low (sink) current characteristics.

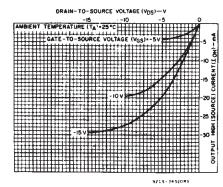


Fig. 3 — Typical output high (source) current characteristics.

STATIC ELECTRICAL CHARACTERISTICS

CHARACTER- ISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							
	٧o	VIN	-					+25			UNITS
	(V)	(V)		-55	-40	+85	+125	Min.	Тур.	Mex.	
Quiescent Device Current,	_	0,5	5	5	5	150	150	_	0.04	5	
	-	0,10	10	10	10	300	300	-	0.04	10	
IDD Max.	-	0,15	15	20	20	600	600	_	0.04	20	μΑ
	_	0,20	20	100	100	3000	3000		0.08	100	1
Output Low	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1 .	-	
(Sink) Current	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6		
IOL Min.	1.5	0,15	15	4.2	4	2.8	2.4	3 4	6.8	_	1
Output High (Source)	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1		mA
	2.5	0,5	5	-2	1.8	-1.3	-1.15	-1.6	-3.2	-]
Current, IOH Min.	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	-	[
IOH WIII.	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	-	
Output Voltage:	-	0,5	5	0.05				-	0	0.05	
Low Level, VOL Max.	_	0,10	10	0.05				-	0	0.05	
AOL Max.	_	0,15	15	0.05				_	0	0.05	
Output Voltage:		0,5	5	4.95				4.95	5	-	ľ
High-Level,		0,10	10	9.95				9.95	10	-	
VOH Min.	-	0,15	15	14.95				14.95	15	-	
Input Low Voltage,	0.5, 4.5	_	5	1.5				_	-	1.5	
	1, 9	_	10	3					_	3	
VIL Max.	1.5,13.5	_	15	4				_	_	4	v
Input High Voltage, VIH Min.	0.5, 4.5		5	3.5 3.5				3.5			V
	1, 9		10	7				7	_		
	1.5,13.5	•	15	11				11	_		
Input Current IJN Max.		0,18	18	±0.1	±0.1	±1	±1	-	±10-5	±0.1	μΑ

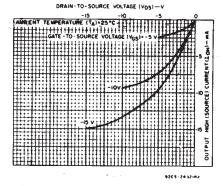


Fig. 4 — Minimum output high (source) current characteristics.

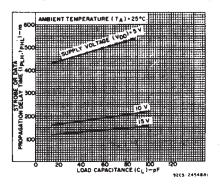


Fig. 5 — Typical strobe or data propagation delay time vs. load capacitance.

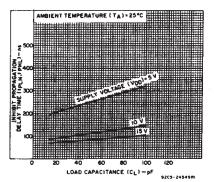


Fig. 6 — Typical inhibit propagation delay time vs. load capacitance.

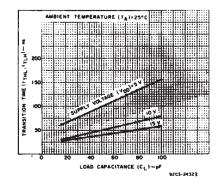


Fig. 7 — Typical low-to-high transition time vs. load capacitance.

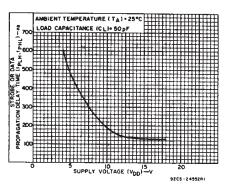


Fig. 8 — Typical strobe or data propagation delay time vs. supply voltage.

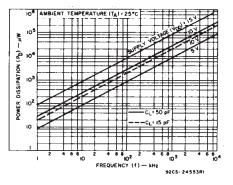


Fig. 9- Typical power dissipation vs. frequency.

CD4514B, CD4515B Types

DYNAMIC ELECTRICAL CHARACTERISTICS at T_A = 25°C; Input t_r , t_f = 20 ns, C_L = 50 pF, R_L = 200 $\kappa\Omega$

	TEST COND	LIMITS			
CHARACTERISTIC		V _{DD}	Тур.	Max.	UNITS
Propagation Delay Time: tpHL, tpLH Strobe or Data		5 10 15	485 185 135	970 370 270	
Inhibit		5 10 15	250 110 85	500 220 170	ns
Transition Time, t _{TLH} , t _{THL}		5 10 15	100 50 40	200 100 80	
Minimum Strobe Pulse Width, t _W		5 10 15	125 50 40	250 100 75	ns
Minimum Data Setup Time, t _S		5 10 15	75 35 20	150 70 40	ns
Input Capacitance, CIN	Any Input	_	5	7.5	рF

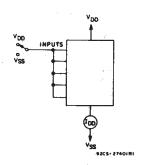


Fig. 10 - Quiescent device current test circuit.

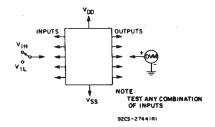


Fig. 11 + Input voltage test circuit.

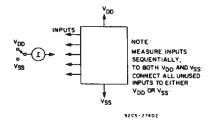


Fig. 12 - Input current test circuit.

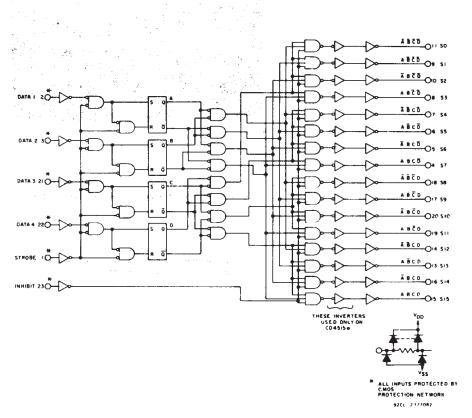
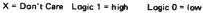


Fig. 13 - Logic diagram for CD4514B and CD4515B,

CD4514B, CD4515B Types

DECODE TRUTH TABLE (Strobe = 1)

INHIBIT	DECODER INPUTS		R	SELECTED OUTPUT		
	D	С	В	A	CD4514B = Logic 1 (High) CD4515B = Logic 0 (Low)	
0 0 0	0000	0000	0 0 1 1	0 1 0 1	\$0 \$1 \$2 \$3	
0 0 0	0000	1 1 1	0 0 1	0 1 0 1	S4 S5 S6 S7	
0 0 0	1 1 1	0000	0 0 1 1	0 1 0 1	\$8 \$9 \$10 \$11	
0 0 0	1 1 1	1 1 1 1	0 0 1 1	0 1 0 1	\$12 \$13 \$14 \$15	
1	х	х	x	х	All Outputs = 0, CD4514B All Outputs = 1, CD4515B	



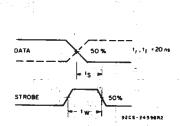
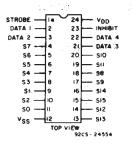
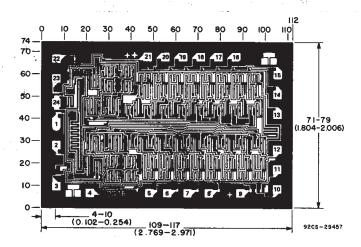


Fig. 14 — Waveforms for setup time and strobe pulse width.



CD4514B CD4515B TERMINAL ASSIGNMENT



Dimensions and Pad Layout for CD4515B Chip (Dimensions and pad layout for the CD4514B are identical)

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils $(10^{-3} \, \text{inch})$.

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